



N-Channel 20-V (D-S) MOSFET

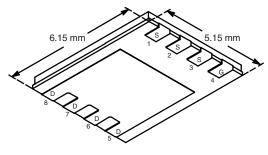
PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a	Q _g (Typ.)			
20	0.0048 at V _{GS} = 10 V	35	12.7 nC			
	0.0063 at V _{GS} = 4.5 V	35	12.7 110			

FEATURES

- Halogen-free
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested

RoHS COMPLIANT

PowerPAK® SO-8

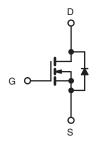


Bottom View

Ordering Information: SiR410DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

- DC/DC Converter
 - Notebook
 - POL



N-Channel MOSFET

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	20 ± 20		
Gate-Source Voltage		V _{GS}			
	T _C = 25 °C		35 ^a		
Continuous Drain Current (T = 150 °C)	T _C = 70 °C		35 ^a		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	23 ^{b, c}	^	
	T _A = 70 °C		18.6 ^{b, c}	A	
Pulsed Drain Current		I _{DM}	60		
Avalanche Current	L = 0.1 mH	I _{AS}	35		
Avalanche Energy	L=0.11IIII	E _{AS}	61	mJ	
Continuous Source-Drain Diode Current	T _C = 25 °C		30	Α.	
Continuous Source-Diam Diode Current	T _A = 25 °C	I _S	3.5 ^{b, c}	^	
	T _C = 25 °C		36		
Maximum Power Dissipation	T _C = 70 °C	P _D	23	w	
Maximum i ower bissipation	T _A = 25 °C	' D	4.2 ^{b, c}	• • • • • • • • • • • • • • • • • • • •	
	T _A = 70 °C		2.7 ^{b, c}		
Operating Junction and Storage Temperature	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Tempera		260			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R_{thJA}	25	30	°C/W		
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	2.9	3.5	0/11		

Notes:

- a. Package Limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s
- d. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 70 °C/W.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	-					
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			٧
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050 A		19		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 5.3		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.2		2.5	٧
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V _{DS} = 20 V, V _{GS} = 0 V			1	_
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			5	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α
D : 0	Б	V _{GS} = 10 V, I _D = 20 A		0.0048		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 19.4 A		0.005	0.0063	Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		70		S
Dynamic ^b				I		
Input Capacitance	C _{iss}			1600		
Output Capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		500		pF
Reverse Transfer Capacitance	C _{rss}			200		
T. 10 . 0	Qg	$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		27	41	nC
Total Gate Charge				16.7	25	
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 19 \text{ A}$		4.5		
Gate-Drain Charge	Q _{gd}			3.5		
Gate Resistance	R_g	f = 1 MHz		1.3	2.6	Ω
Turn-On Delay Time	t _{d(on)}			25	40	
Rise Time	t _r	V_{DD} = 10 V, R_L = 1 Ω		15	25	ns
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 10 A, V_{GEN} = 4.5 V, R_g = 1 Ω		30	45	
Fall Time	t _f			15	25	
Turn-On Delay Time	t _{d(on)}			12	20	
Rise Time	t _r	V_{DD} = 10 V, R_L = 1 Ω		10	15	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 10$ A, $V_{GEN}=10$ V, $R_g=1$ Ω		25	40	
Fall Time	t _f			10	15	
Drain-Source Body Diode Characteristi	cs			II.		
Continuous Source-Drain Diode Current	I _S	$T_C = 25 ^{\circ}C$			35	А
Pulse Diode Forward Current	I _{SM}				60	^
Body Diode Voltage	V_{SD}	I _S = 10 A, V _{GS} = 0 V		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			30	45	ns
Body Diode Reverse Recovery Charge	Q_{rr}	I _F = 10 A, dI/dt = 100 A/μs, T _{.I} = 25 °C		21	35	nC
Reverse Recovery Fall Time	t _a	$I_F = 10 \text{ A}$, $I_{I} = 100 \text{ A/}\mu\text{S}$, $I_{J} = 25 ^{\circ}\text{C}$		17		
everse Recovery Rise Time t _b				13		ns

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

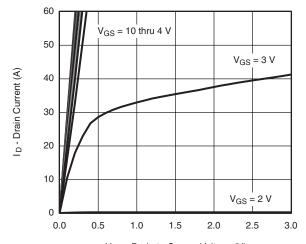
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





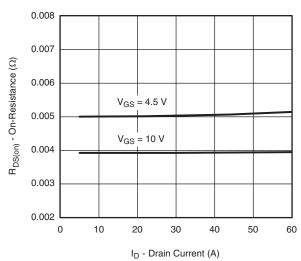


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

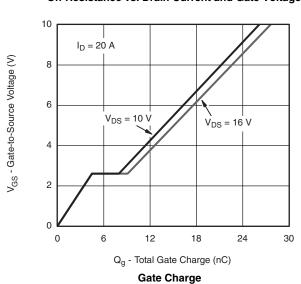


V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics



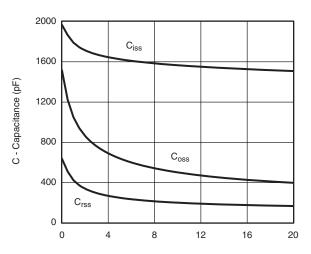
On-Resistance vs. Drain Current and Gate Voltage



20 16 ID - Drain Current (A) 12 T_C = 25 °C 8 4 T_C = 125 °C $T_C = -55$ °C 0 0.0 0.5 1.0 2.0 2.5 3.0 1.5

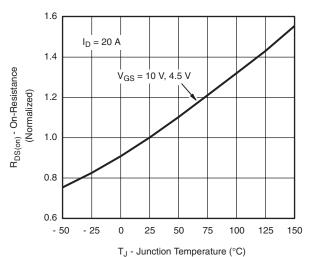
V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



 $V_{\mbox{\footnotesize DS}}$ - Drain-to-Source Voltage (V)

Capacitance

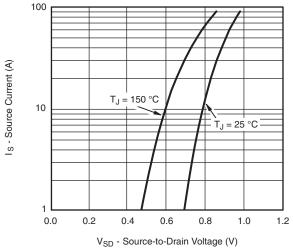


On-Resistance vs. Junction Temperature

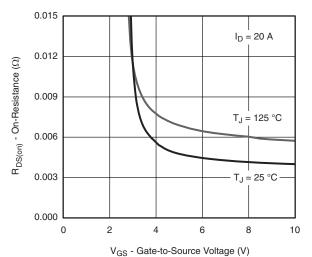
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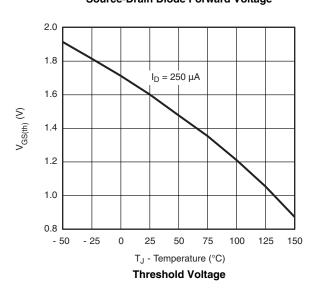
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

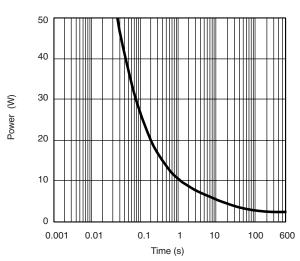


Source-Drain Diode Forward Voltage

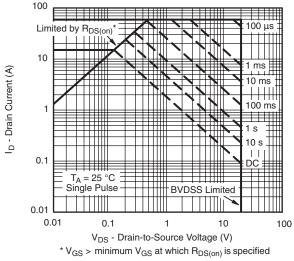


On-Resistance vs. Gate-to-Source Voltage





Single Pulse Power (Junction-to-Ambient)



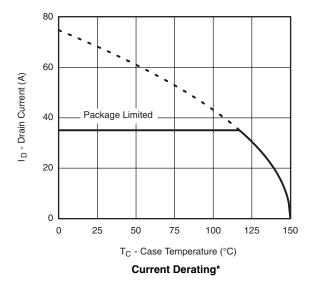
Safe Operating Area, Junction-to-Ambient

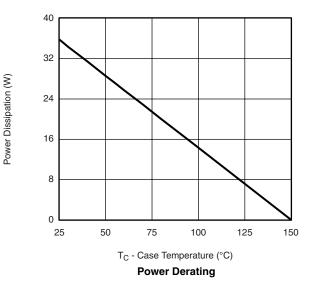






TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





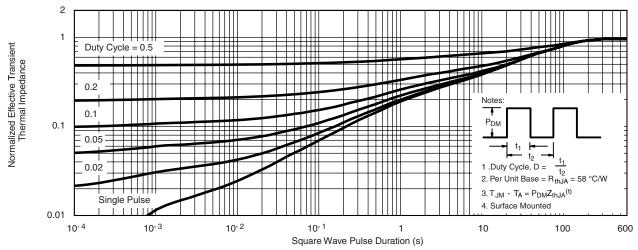
Document Number: 68997 S-82586-Rev. A, 27-Oct-08

^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

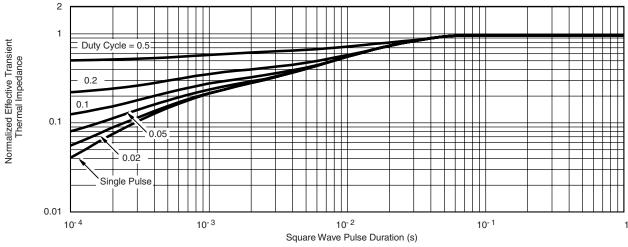
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



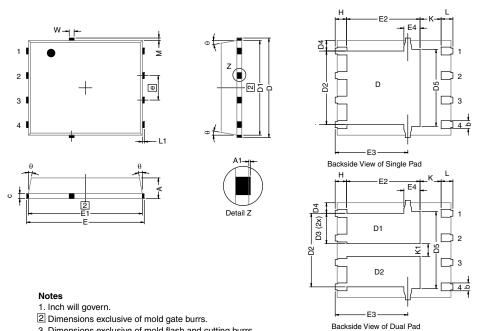
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?68997.



DWG: 5881

PowerPAK® SO-8, (Single/Dual)



	3. Dimensions exclusive	of mold flash and cuttin	g burrs.					
DIM.		MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
A	0.97	1.04	1.12	0.038	0.041	0.044		
A1		-	0.05	0	-	0.002		
b	0.33	0.41	0.51	0.013	0.016	0.020		
С	0.23	0.28	0.33	0.009	0.011	0.013		
D	5.05	5.15	5.26	0.199	0.203	0.207		
	4.00	4.00	F 00	0.400	0.400	0.407		

Α	0.97	1.04	1.12	0.038	0.041	0.044		
A1		-	0.05	0	-	0.002		
b	0.33	0.41	0.51	0.013	0.016	0.020		
С	0.23	0.28	0.33	0.009	0.011	0.013		
D	5.05	5.15	5.26	0.199	0.203	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.56	3.76	3.91	0.140	0.148	0.154		
D3	1.32	1.50	1.68	0.052	0.059	0.066		
D4		0.57 typ.		0.0225 typ.				
D5		3.98 typ.		0.157 typ.				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	5.79	5.89	5.99	0.228	0.232	0.236		
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144		
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151		
E3	3.68	3.78	3.91	0.145	0.149	0.154		
E4 (for AL product)	0.58 typ.				0.023 typ.			
E4 (for other product)		0.75 typ.		0.030 typ.				
е		1.27 BSC		0.050 BSC				
K (for AL product)		1.45 typ.		0.057 typ.				
K (for other product)		1.27 typ.		0.050 typ.				
K1	0.56	-	=	0.022	-	=		
Н	0.51	0.61	0.71	0.020	0.024	0.028		
L	0.51	0.61	0.71	0.020	0.024	0.028		
L1	0.06	0.13	0.20	0.002	0.005	0.008		
θ	0°	-	12°	0°	-	12°		
W	0.15	0.25	0.36	0.006	0.010	0.014		
M	0.125 typ.			0.005 typ.				
ECN: C13-0702-Rev. K, 20)-May-13			•				

Revison: 20-May-13 Document Number: 71655



RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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